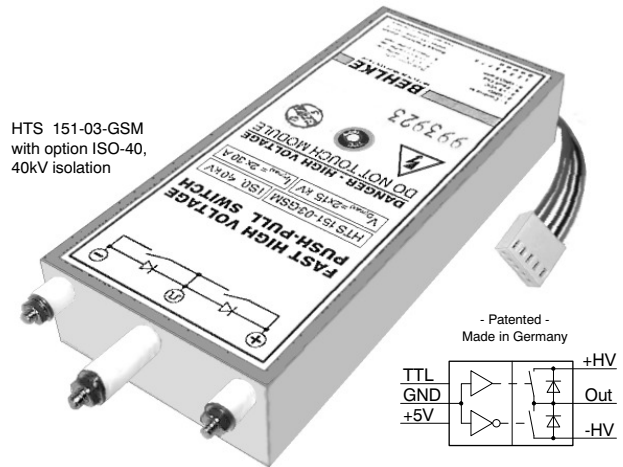


FAST HIGH VOLTAGE TRANSISTOR SWITCHES

The switching modules of the series HTS-GSM consist of two identical MOSFET switching paths that form a so-called half bridge circuit respectively push-pull circuit. Both switching paths are controlled by a common driver, which also provides a logic signal negation for one of the switches. The switches are mutually passively locked, so that a short in the bridge is excluded under all circumstances, including if the control input is disturbed by electromagnetic interferences (due to bad EMC design, for example). Especially in pulse generator applications with capacitive load, the push-pull principle has considerable advantages in comparison with the conventional circuitry using a single-switch with a working resistor. Push-pull circuits do not require large energy storage capacitors for a low pulse drop and, because there are no working resistor power losses, the efficiency of a push-pull pulser is excellent regardless of pulse width, frequency and duty cycle. The pulsers draw only currents for charging the connected load capacitance. Thanks to an extremely precise timing of the switches, there are also almost no cross currents in the bridge, except peak charging currents of the switch natural capacitances.

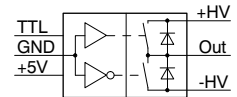
The switches are controlled by positive going signals of 3 to 10 Volts amplitude. Fault conditions as overfrequency, thermal overload (long-term overload) and incorrect auxiliary supply set the switching path A in off-state and the switching path B in on-state. Faults are indicated as an "L" signal at the fault signal output. Without 5VDC supply, both switching paths (A and B) are in off-state. That implies, without 5VDC the output potential could be undefined if the HV is still applied. To ensure a defined high voltage output potential in such cases, pull-up or pull-down resistors must be connected to the output. For further design recommendations, please refer to the general instructions.

HTS 81-06-GSM 2x 8 kV / 60A
HTS 151-03-GSM 2x15kV / 30A



HTS 151-03-GSM with option ISO-40, 40kV isolation

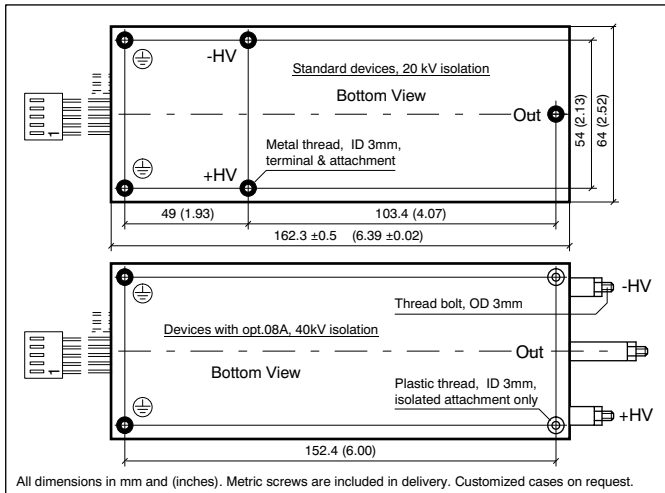
- Patented -
Made in Germany



- Fast transition times, rise time and fall time ~15 ns
- Variable pulse width from 150 ns to infinity
- No pulse drop and very low ripple on the pulse top
- No working resistor power, small buffer capacitors

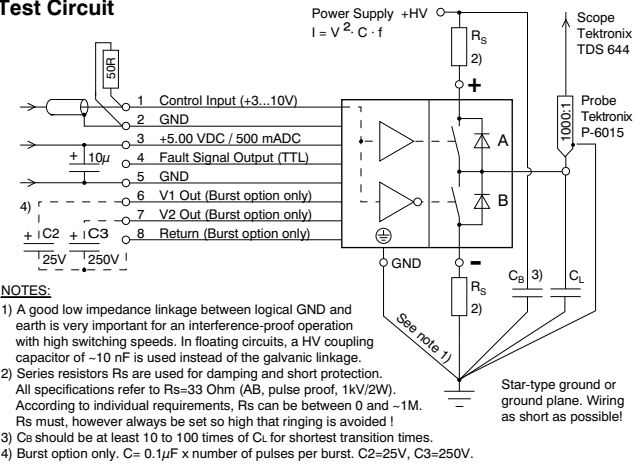
PUSH-PULL

MOSFET TECHNOLOGY

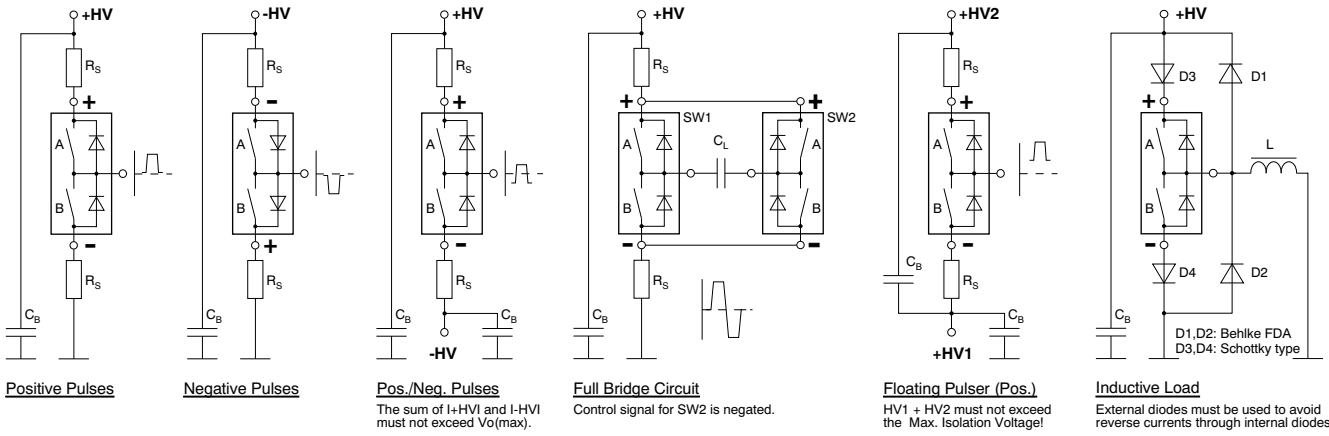


All dimensions in mm and (inches). Metric screws are included in delivery. Customized cases on request.

Test Circuit



Basic Circuits



TECHNICAL DATA

Specification	Symbol	Condition / Comment	81-06-GSM	151-03-GSM	Unit	
Maximum Operating Voltage	$V_{O(max)}$	$I_{off} < 10 \mu ADC$	2 x 8000	2 x 15000	VDC	
Minimum Operating Voltage	$V_{O(min)}$	Increased transition times below $0.1 \times V_{O(max)}$	0		VDC	
Typical Breakdown Voltage	V_{br}	Static voltage, $I_{off} > 1 \text{ mADC}$, $T_{case} = 70^\circ C$	2 x 9500	2 x 18000	VDC	
Galvanic Isolation	V_i	Continuously HV terminals at bottom (Standard) HV terminals at front (Opt.ISO-40)	20000 40000		VDC	
Max. Peak Current Capability	$I_{P(max)}$	$T_{case} = 25^\circ C$ $t_p < 10 \mu s$, duty cycle $< 1\%$	2 x 60	2 x 30	ADC	
Max. Continuous Load Current	I_L	$T_{case} = 25^\circ C$ $T_{fin} = 25^\circ C$ Standard plastic case Opt. ITC, incr. thermal conductivity Opt. CF, cooling fins (air $> 4\text{m/s}$)	2 x 0.91 2 x 1.05 2 x 2.89	2 x 0.41 2 x 0.47 2 x 1.29	ADC	
Static On-Resistance	R_{stat}	$T_{case} = 25^\circ C$ $0.1 \times I_{P(max)}$ $1.0 \times I_{P(max)}$	2 x 8 2 x 18	2 x 36 2 x 90	Ω	
Maximum Off-State Current	I_{off}	$0.8 \times V_O$, $T_{case} = 25...70^\circ C$, reduced I_{off} on request	10		μADC	
Propagation Delay Time	t_d	Resistive Load	150		ns	
Typical Output Transition Time (Rise Time & Fall Time)	t_r, t_f	$0.8 \times V_O$ 10-90% Standard device (Bottom terminals)	$R_S = 33 \Omega$, $C_L = 10 \text{ pF}$ $R_S = 33 \Omega$, $C_L = 50 \text{ pF}$ $R_S = 33 \Omega$, $C_L = 100 \text{ pF}$ $R_S = 33 \Omega$, $C_L = 200 \text{ pF}$ $R_S = 22 \Omega$, $C_L = 1000 \text{ pF}$	7 9 12 19 55	14 18 26 45 80	ns
Minimum Output Pulse Width	$t_{p(min)}$	Reduced output pulse width on request.	150		ns	
Maximum Output Pulse Width	$t_{p(max)}$		No limitation, up to ∞			
Minimum Pulse Spacing	$t_{ps(min)}$	(Switch recovery time)	400		ns	
Typical Output Pulse Jitter	t_j	$V_{aux} = 5.0 \text{ VDC}$ $V_{tr} = 5.0 \text{ VDC}$ Fixed switching frequency, $> 2\text{kHz}$ Sweepled frequency, $< 2\text{kHz}$	0.1 2		ns	
Max. Continuous Switching Frequency	$f_{(max)}$	@ $V_{aux} = 5.00 \text{ VDC}$ Please note possible $P_{d(max)}$ limitations. Increased switching frequency on request.	10		kHz	
Maximum Burst Frequency	$f_{b(max)}$	Use option HFB for > 10 pulses per $20 \mu s$ burst	2.5		MHz	
Maximum Continuous Power Dissipation	$P_{d(max)}$	$T_{case} = 25^\circ C$ $T_{fin} = 25^\circ C$ Standard plastic case Opt. ITC, incr. thermal conductivity Opt. CF, cooling fins (air $> 4\text{m/s}$)	2 x 15 2 x 20 2 x 150		Watts	
Linear Derating		Above $25^\circ C$ Standard plastic case Opt. ITC, incr. thermal conductivity Opt. CF, cooling fins (air $> 4\text{m/s}$)	2 x 0.33 2 x 0.44 2 x 3.33		W/K	
Temperature Range	T_O		-40...70		$^\circ C$	
Typical Natural Capacitance	C_N	Capacitance between + and - terminal of one switch path	$0.1 \times V_{O(max)}$ $0.8 \times V_{O(max)}$	< 90 < 30	pF	
Typical Coupling Capacitance	C_C	Both switches against ground respectively control	< 30		pF	
Reverse Recovery Time of the intrinsic diodes (Parasitic MOSFET Diodes)	t_{rrc}	Note: The internal diodes are too slow to be used periodically in forward direction (danger of bridge-short). Free-wheeling diode networks must be applied in case of inductive load or high stray inductance!	$I_F = 2A$	500...1000		ns
Auxiliary Supply Voltage	V_{aux}	Stabilized to $\pm 5\%$	5.00		VDC	
Auxiliary Supply Current	I_{aux}	$V_{aux} = 5.00 \text{ VDC}$ $T_{case} = 25^\circ C$	@ $f < 1\text{kHz}$ @ f_{max}	< 150 < 1000		mADC
Control Signal	V_{tr}	$> 3\text{VDC}$ recommended for low jitter	3...10		VDC	
Fault Signal Output		Short circuit proof, source/sink current max. 10 mA	Ready = High Fault = Low	≥ 4.0 ≤ 0.8		VDC
Dimensions	$L \times W \times H$	Standard plastic case (Without connectors) With option CF (cooling fins)	163x64x27 163x64x62		mm^3	
Weight		Standard plastic case With option CF (cooling fins)	460 650		g	

Ordering Information

HTS 81-06-GSM Push-pull transistor switch

HTS 151-03-GSM Push-pull transistor switch

Option HFB High frequency burst

Option ITC Increased thermal conductivity

Option CF Cooling fins, non isolated, for vertical air stream only

Option PIN-C Control connection: Pins instead of pigtail & plug

Option ISO-40* 40kV isolation, HV front terminals

Option ISO-80* 80kV isolation, HV front terminals, enlarged case

* Not recommended for switching speeds $< 15\text{ns}$